

Silicon PNP Power Transistors

2SA1671

DESCRIPTION

- With TO-3PML package
- Complement to type 2SC4386

APPLICATIONS

- Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

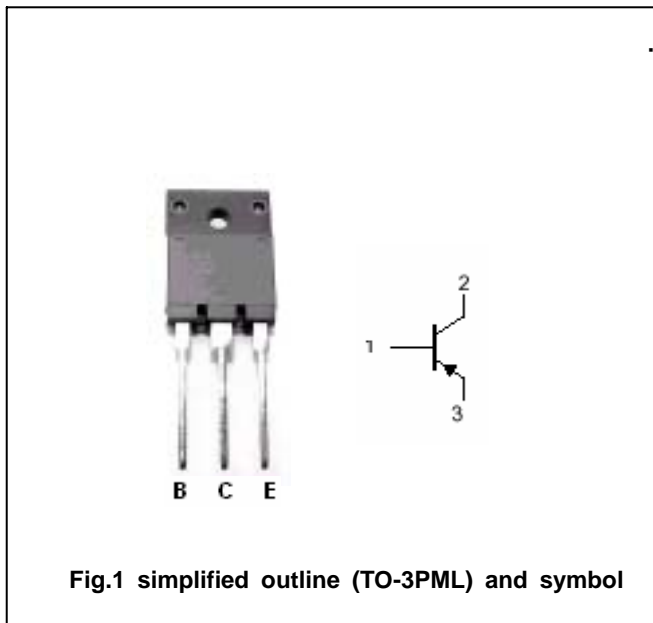


Fig.1 simplified outline (TO-3PML) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-8	A
I_B	Base current		-3	A
P_C	Collector power dissipation	$T_C=25$	75	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-50mA; I _B =0	-120			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA; I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3 A; I _B =-0.3 A			-0.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-120V; I _E =0			-10	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-10	μ A
h _{FE}	DC current gain	I _C =-3A ; V _{CE} =-4V	50		180	
f _T	Transition frequency	I _C =-0.5A ; V _{CE} =-12V		20		MHz

◆ h_{FE} classifications

O	P	Y
50-100	70-140	90-180

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PACKAGE OUTLINE

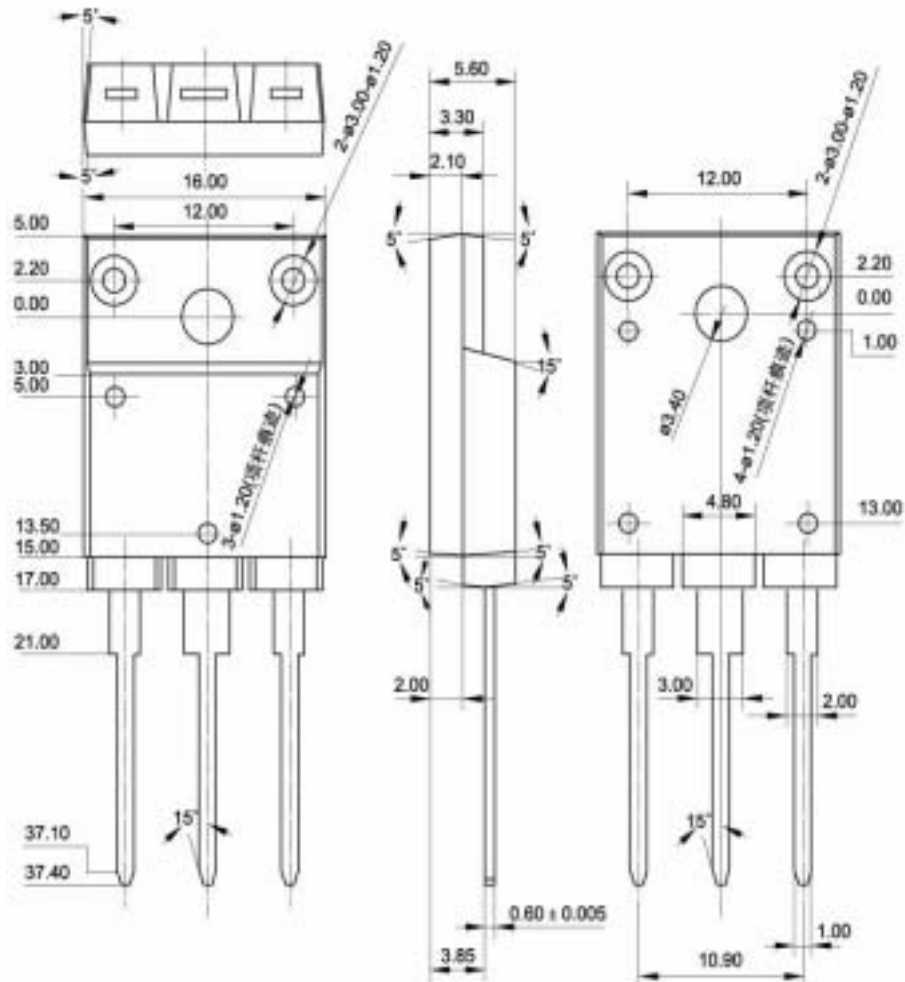


Fig.2 Outline dimensions